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Inclosure Material:

Metal

Overall Length:

0.320 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-111

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

0.424 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

80.0 collector to base voltage/static/emitter open and 80.0 breakdown voltage, collector to emitter, sustained and 5.0 emitter to base voltage, static, collector open

Current Rating Per Characteristic:

5.00 amperes source cutoff current

Power Rating Per Characteristic:

28.0 watts small-signal input power, common-collector

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: pnp

Test Data Document:

82577-928402 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unf

Terminal Type And Quantity:

3 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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